Product data sheet

1. Product profile

1.1. General description

NPN medium power transistors in a medium power SOT223 (SC73) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package	NPN comlement	
	Nexperia	JEDEC	
BCP54T	SOT223	SC-73	BCP51T
BCP54-10T			BCP51-10T
BCP54-16T		l	BCP51-16T

1.2. Features and benefits

- High collector current capability I_C and I_{CM}
- · Three current gain selections
- · High power dissipation capability
- · AEC-Q101 qualified

1.3. Applications

- · Linear voltage regulators
- MOSFET drivers
- · High-side switches
- Power management
- Amplifiers

1.4. Quick reference data

Table 2. Quick reference data

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I _C	collector current		-	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	2	Α



45 V, 1 A NPN medium power transistors

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
h_{FE}	DC current gain						
	BCP54T	V _{CE} = 2 V; I _C = 150 mA	[1]	63	-	250	
	BCP54-10T		[1]	63	-	160	
	BCP54-16T		[1]	100	-	250	

^[1] pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02$

2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		
3	E	emitter		в
4	С	collector	∃1 ∃2 ∃3	Ė
				sym123

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
BCP54T	SC-73	plastic, surface-mounted package with increased heatsink;	SOT223			
BCP54-10T		4 leads				
BCP54-16T						

4. Marking

Table 5. Marking

Type number	Marking code
BCP54T	BCP54T
BCP54-10T	P5410T
BCP54-16T	P5416T

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5. Limiting values

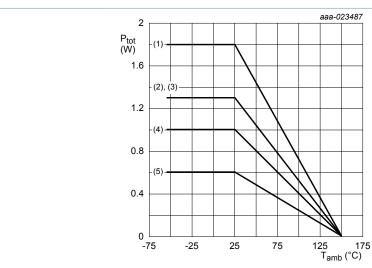
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	45	V
V _{CEO}	collector-emitter voltage	open base		-	45	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _B	base current			-	0.2	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	0.3	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1	W
			[3]	-	1.3	W
			[4]	-	1.3	W
			[5]	-	1.8	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint.
- [5] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm.²



- (1) FR4 PCB; 4-layer copper; 1 cm²
- (2) FR4 PCB; single-sided copper; 6 cm²
- (3) FR4 PCB; 4-layer copper; standard footprint
- (4) FR4 PCB; single-sided copper; 1 cm²
- (5) FR4 PCB; single-sided copper; standard footprint

Fig. 1. Power derating curves

BCP54T_SER

45 V, 1 A NPN medium power transistors

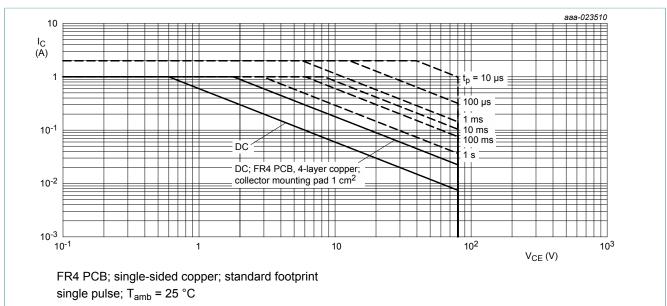


Fig. 2. Safe operating area; junction to ambient; continous and peak collector currents as a funtion of collecoremitter voltage

45 V, 1 A NPN medium power transistors

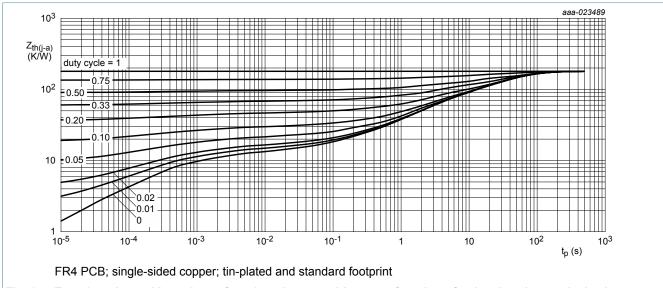
6. Thermal characteristics

Table 7. Thermal characteristics

 T_{amb} = 25 °C unless otherwise specified.

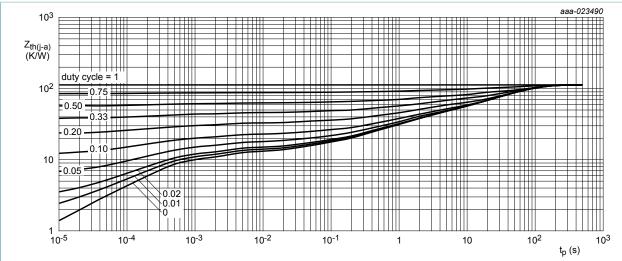
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal	thermal resistance from junction to ambient	in free air	[1]	-	-	209	K/W
			[2]			125	K/W
			[3]			97	K/W
			[4]	-	-	97	K/W
			[5]	-	-	70	K/W
R _(j-sp)	thermal resistance from junction to solder point			-	-	18	K/W

- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm². Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 6 cm². [3]
- Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint. [4]
- [5] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm².



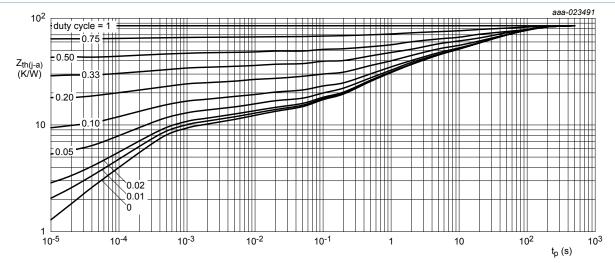
Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

45 V, 1 A NPN medium power transistors



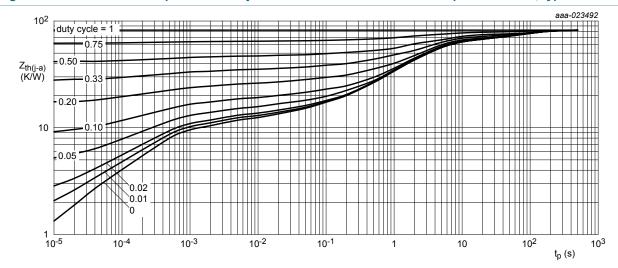
FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm²

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 6 cm²

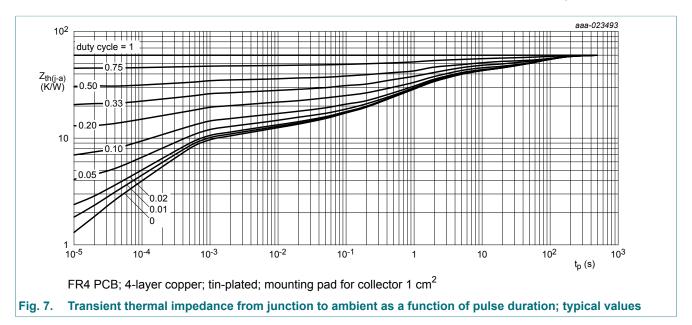
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin-plated and standard footprint

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

45 V, 1 A NPN medium power transistors



7. Characteristics

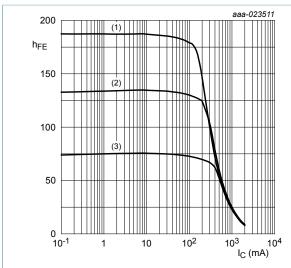
Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A		45	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 2 mA; I _E = 0 A		45	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	I _E = 100 μA; I _C = 0 A		5	-	-	V
I _{CBO}	collector-base	V _{CB} = 30 V; I _E = 0 A		-	-	100	nA
	cut-off current	$V_{CB} = 30 \text{ V}; I_{E} = 0 \text{ A}; T_{j} = 150 \text{ °C}$		-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A		-	-	100	nA
h _{FE} DC current gain						'	
	BCP54T, -10T, -16T	V _{CE} = 2 V; I _C = 5 mA		63	-	-	
		V _{CE} = 2 V; I _C = 500 mA	[1]	40	-	-	
	BCP54T	V _{CE} = 2 V; I _C = 150 mA	[1]	63	-	250	
	BCP54-10T	V _{CE} = 2 V; I _C = 150 mA	[1]	63	-	160	
	BCP54-16T	V _{CE} = 2 V; I _C = 150 mA	[1]	100	-	250	
V _{CEsat}	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA	[1]	-	-	500	mV
V_{BE}	base-emitter voltage	V _{CE} = 2 V; I _C = 500 mA	[1]	-	-	1	V
f _T	transition frequency	V _{CE} = 5 V; I _C = 50 mA; f = 100 MHz		100	155	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	4.5	-	pF

[1] pulsed; $t_0 \le 300 \,\mu s$; $\delta \le 0.02$

45 V, 1 A NPN medium power transistors



$$V_{CE} = 2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. DC current gain as a function of collector current; typical values

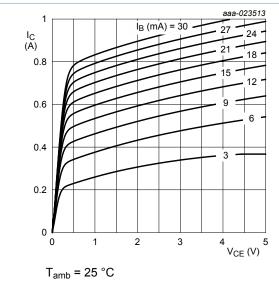
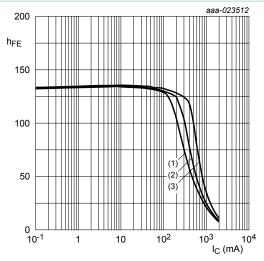


Fig. 10. Collector current as a function of collectoremitter voltage; typical values



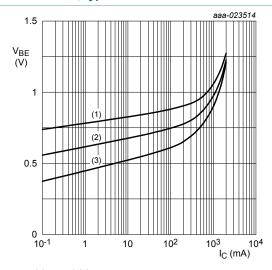
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$V_{CE} = 1 V$$

(2)
$$V_{CE} = 2 V$$

(3)
$$V_{CE} = 5 V$$

Fig. 9. DC current gain as a function of collector current; typical values



$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

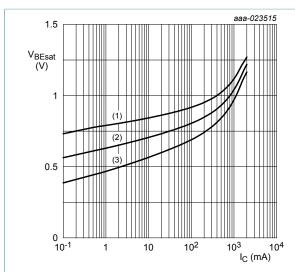
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = 100 °C

Fig. 11. Base-emitter voltage as a function of collector current; typical values

8 / 14

45 V, 1 A NPN medium power transistors



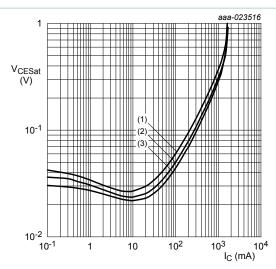
$$I_C/I_B = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. Base-emitter saturation voltage as a function of Fig. 13. Collector-emitter saturation voltage as a collector current; typical values



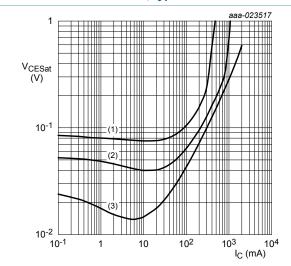
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = -55 °C

function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 5$$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

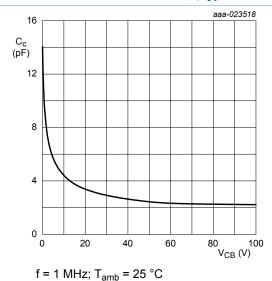
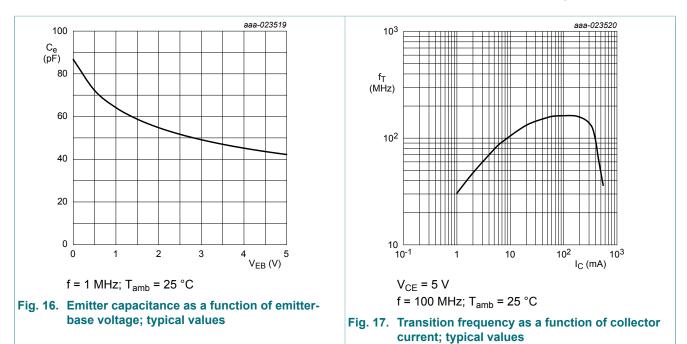


Fig. 15. Collector capacitance as a function of collector-

base voltage; typical values

45 V, 1 A NPN medium power transistors

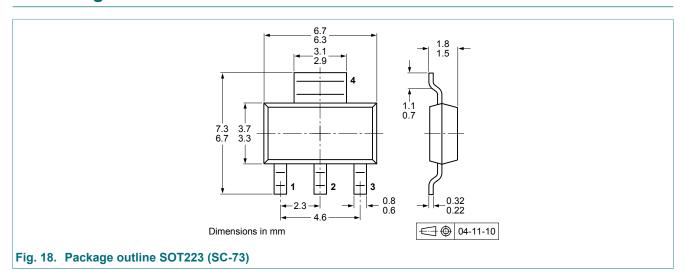


8. Test information

8.1. Quality information

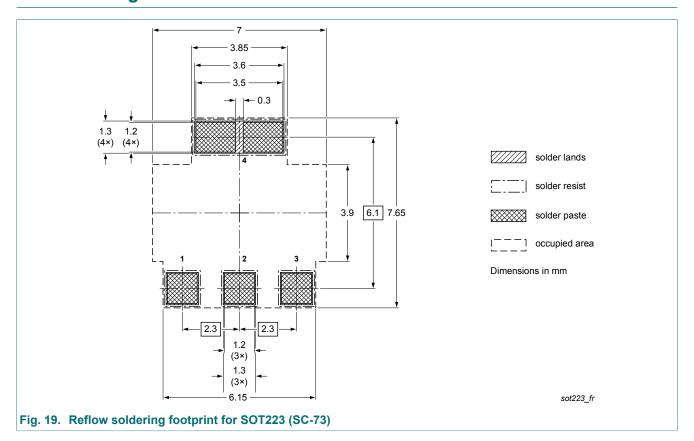
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

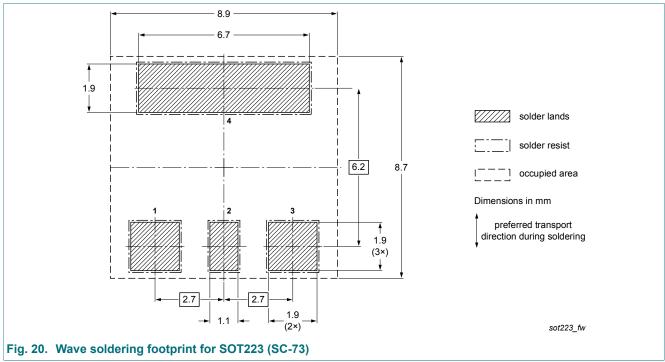
9. Package outline



45 V, 1 A NPN medium power transistors

10. Soldering





11 / 14

45 V, 1 A NPN medium power transistors

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BCP54T_SER v.1	20190429	Product data sheet	-	-

45 V, 1 A NPN medium power transistors

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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45 V, 1 A NPN medium power transistors

Contents

1. Product profile	1
1.1. General description	1
1.2. Features and benefits	1
1.3. Applications	1
1.4. Quick reference data	1
2. Pinning information	2
3. Ordering information	2
4. Marking	2
5. Limiting values	3
6. Thermal characteristics	5
7. Characteristics	7
8. Test information	10
8.1. Quality information	10
9. Package outline	10
10. Soldering	
11. Revision history	12
12. Legal information	13

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